Fast electronics / detector options

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EIC Polarimetry working group

Improving speed of detectors

- For faster repetition rates, it is desirable to have detector response faster than bunch frequency (relevant for electron and ion polarimetry)
- Can have very segmented detector
- Solid state detector actually fast collection time but small charge, typically need shaping and high gain amplification
- Need to be close from detector for best signal to noise ratio and timing resolution

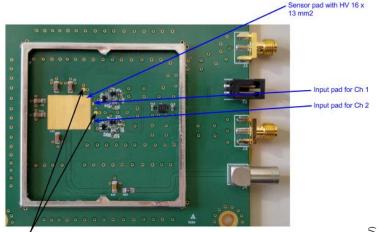
Detectors side

- Detector options
 - Silicon
 - MAPS
 - Diamond
 - LGAD
- Fast preamplifiers
 - TOTEM Kansas preamp
 - Alphacore preamp:
 - ASIC 8 channels
 - VMM3 chip (designed for GEM / Micromegas)
 - 64 channels

Electronics for very fast detectors

TOTEM electronics designed by Kansas University

A two channels board was designed and manufactured for the characterization of different solid state detectors.



The board was optimized to achieve a good time precision with different sensors, however it can be modified to have an output signal shorter (but less precise)

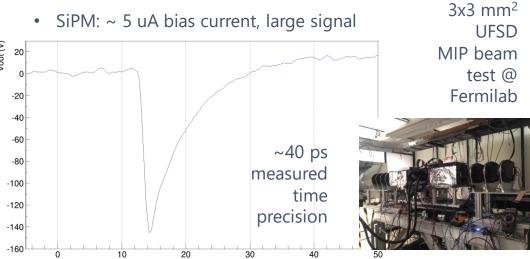
<u>Test of Ultra Fast Silicon Detectors for Picosecond Time</u>
Measurements with a New Multipurpose Read-Out Board

Guard ring pad (if present)

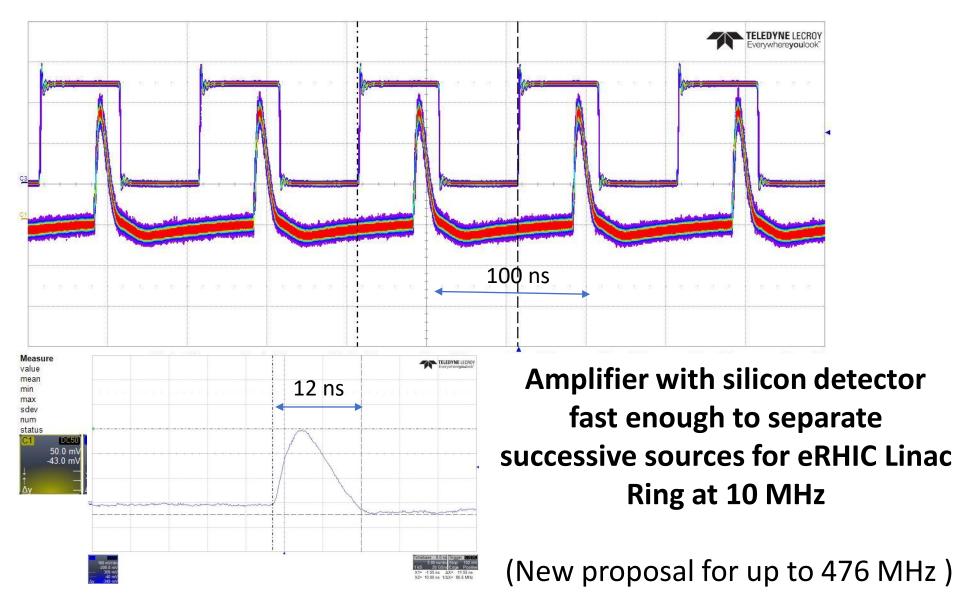
Sensors up to 16x13 mm² can be glued and bonded.

The components can be easily adapted to accommodate:

- Diamond sensors: ~1 nA bias current, both polarities, small signal
- Silicon sensors: ~100 nA bias current, small signal
- UFSD ~100 nA bias current, ~ larger signal

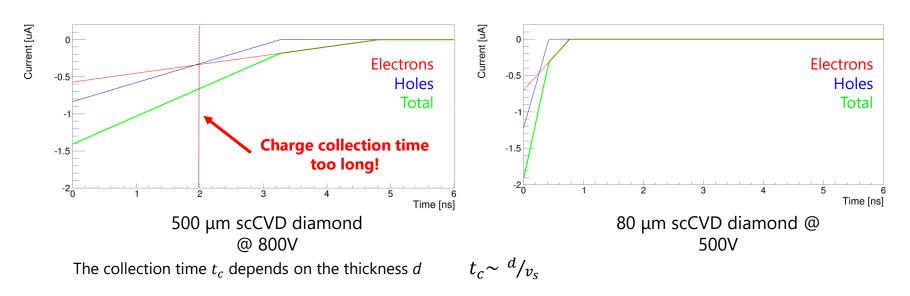


Silicon pulsed with laser at 10 MHz



Fast detector R&D

Diamond sensors are among the fastest available



 $Q_c \sim d$

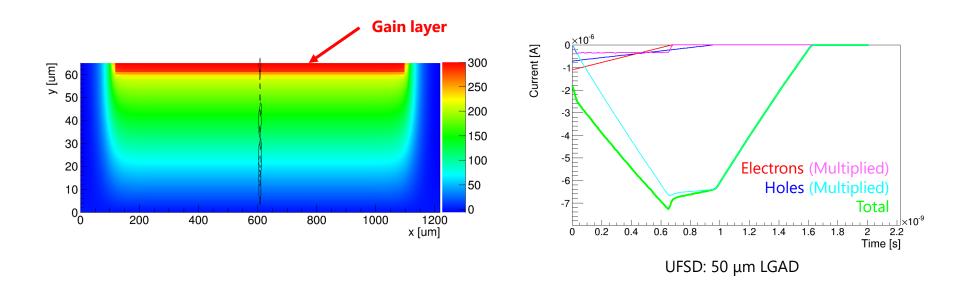
 $|i_{MAX}| \sim Q_c/t_c$

NOTE: the collected charge $Q_c = \int i(t) dt$ also depends on the thickness d

However, the deep current mainly depends on the carriers' velocities, i.e. electric field

Fast detector R&D

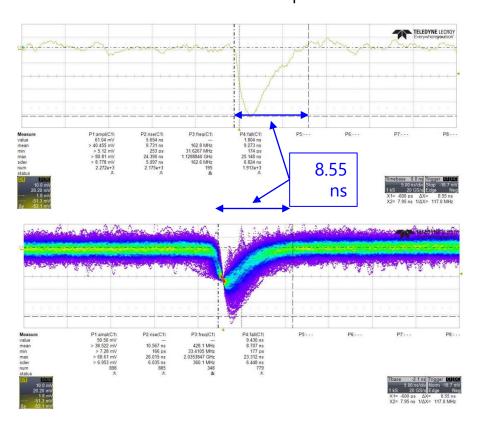
Ultra Fast Silicon Detectors: as fast as diamond, but with a gain layer!

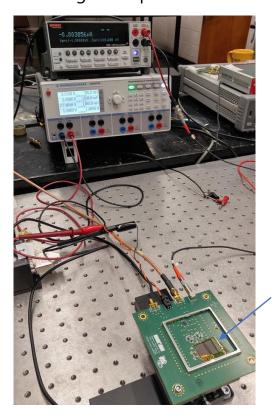


ast collection time (50 μ m thick) and larger signals, thanks to the gain layer

Electronics for very fast detectors

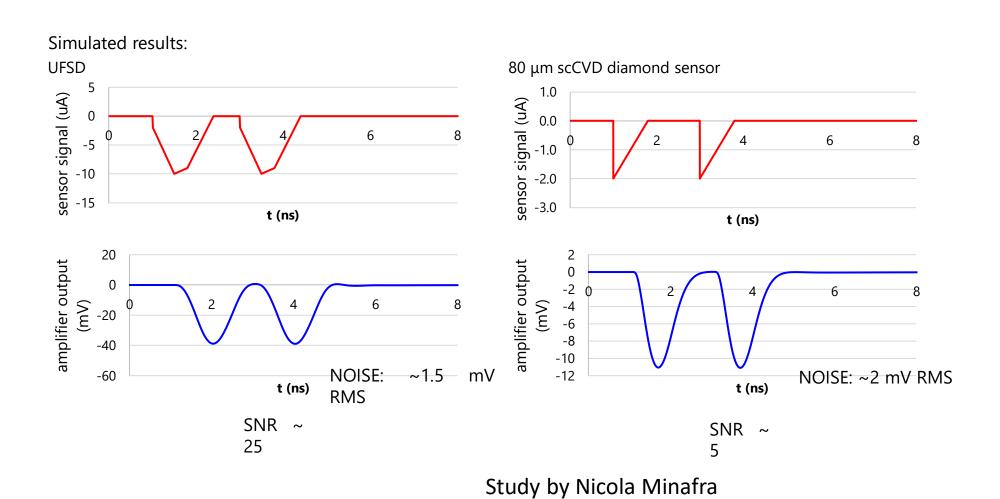
This board was also used to test the performance of a diamond sensor using a Sr^{90} β - source.





500 μm pcCVD diamond

Fast detector R&D



Integrated ASIC

- Was looking at VMM3 chip
 - Gain: 0.5,1,3,4,4.5,6,9,12,16 mV/fC
 - Integration time: 25,50,100,200 ns
 - Possibility for triggering
 - Different reading mode
 - Multiplexed analog amplitude and timing
 - Digitized 10 bit amplitude 20 bit timestamp
 - ART (streaming mode)

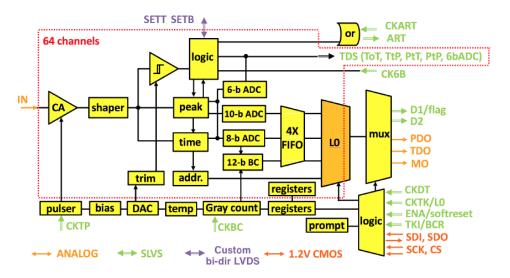


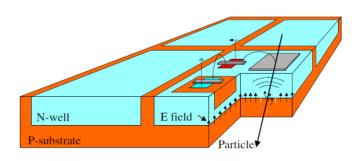
Figure 1: Architecture of VMM3.



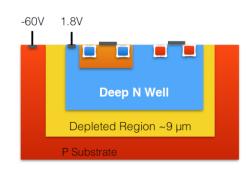
MAPS option

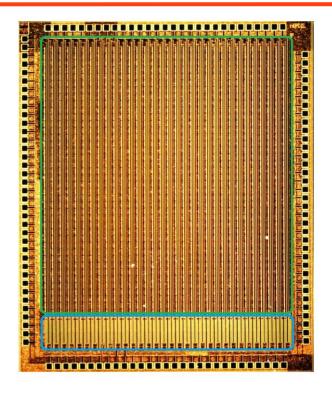
- Silicon detector can be thinned up to 80 um
- Integrated analog and digital electronics
- Well adapted for pixelized detector since less external electronics
- Cons: not sure about energy resolution, mostly optimized for timing but chip detector could be tailored to need

HV MAPS



- Pixellized detector MuPix for Mu3e
- 80 um x 80 um x 50 um
- Electronics in integrated with pixel (amplification and readout)
- Being investigated by University of Manitoba
- Timing resolution around 16 ns
- 380 Mrad radiation hardness
- Should work in vacuum
- Might work at low temperature





32x40 pixels Mupix4

Sampling chips

- Analog sampling
 - PSEC4, DRS4: 1 to 10 GSps 8 channels
 - ASOC: 1 to 3 GSps 4 channels
 - AARDVARC: 10 to 14 Gsps 4 channels 12 bits

• FADCs :

- JLAB FADC: 250 MHz 12 bit 16 channels
- Alphacore ASIC: 10 bit 0.5,1,3 Gsps 6 bit 10 Gsps
- CAEN, Struck:
 - 250 MHz 14 bit 8 or 16 channels
 - 500 MHz 14 bit 8 or 16 channels
 - 1 GHz to 2 GHz 10 bit
 - 4 GHz 10 bit 2 channels